

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

Inventor(s): MIYASHITA et al.

Filed: Herewith

Title: SEMICONDUCTOR DEVICE COMPRISING METAL SILICIDE FILMS FORMED TO COVER GATE ELECTRODE AND SOURCE-DRAIN DIFFUSION LAYERS AND METHOD OF MANUFACTURING THE SAME

July 30, 2001

PRELIMINARY AMENDMENT

Hon. Commissioner of Patents
Washington, D.C. 20231

Sir:

Please amend this application as follows:

IN THE SPECIFICATION:

At the top of the first page, just under the title, insert:

1. --This is a Continuation-In-Part Divisional
 Continuation Substitute Application (MPEP 201.09) of
 1(a) National Application No. 09/164,343 filed October 1, 1998.
 1(b) International Application No. PCT/_/_/
 filed ___ which designated the U.S.--

2. --This application claims the benefit of U.S. Provisional Application No.
 60/_/_ filed ___--

Respectfully submitted,

PILLSBURY WINTHROP LLP
Intellectual Property Group

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